

## INCHANGE SEMICONDUCTOR

# isc N-Channel MOSFET Transistor

## IRFU3710Z

### • FEATURES

- With TO-251(IPAK) packaging
- High speed switching
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

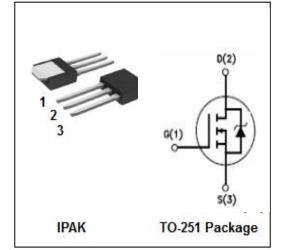
### APPLICATIONS

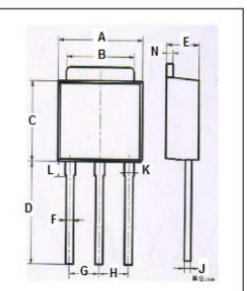
- Power supply
- DC-DC converters
- Motor control
- Switching applications

ABSOLUTE MAXIMOW RATINGS(Ta=25 C)					
SYMBOL	PARAMETER	VALUE	UNIT		
V <sub>DSS</sub>	Drain-Source Voltage	100	V		
V <sub>GSS</sub>	Gate-Source Voltage	±20	∧v		
I <sub>D</sub>	Drain Current-Continuous	56	A		
I <sub>DM</sub>	Drain Current-Single Pulsed	220	А		
PD	Total Dissipation	140	W		
Tj	Operating Junction Temperature	-55~175	°C		
T <sub>stg</sub>	Storage Temperature	-55~175	°C		

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	1.05	°C/W	
Rth(ch-a)	Channel-to-ambient thermal resistance	40	°C/W	





	mm	
DIM	MIN	MAX
Α	6.40	6.48
В	5.10	5.50
С	5.80	6.20
D	9.20	9.60
E	2.20	2.40
F	0.50	0.70
G	2.09	2.49
Н	2.09	2.49
J	0.40	0.60
Κ	0.70	0.90
L	1.60	2.00
N	0.40	0.60

#### isc website: www.iscsemi.cn

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## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

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### ELECTRICAL CHARACTERISTICS

 $T_{\text{C}}\text{=}25^\circ\!\!\mathbb{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA	100			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.1mA	2.0		4.0	V
$R_{\text{DS(on)}}$	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =33A		15	18	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±0.2	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 100V; V <sub>GS</sub> = 0V;Tj=25℃ V <sub>DS</sub> = 100V; V <sub>GS</sub> = 0V;Tj=125℃			20 250	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =33A, V <sub>GS</sub> =0V			1.3	v

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